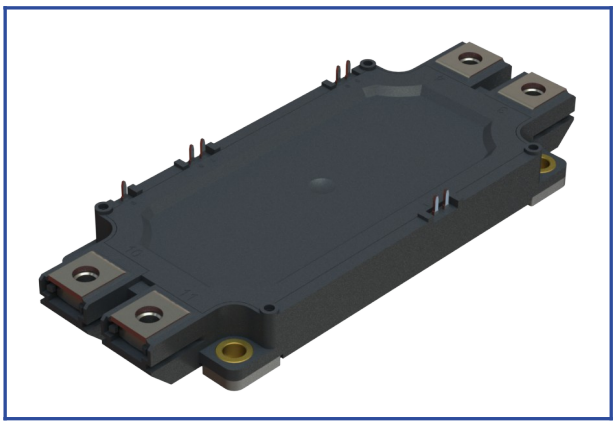
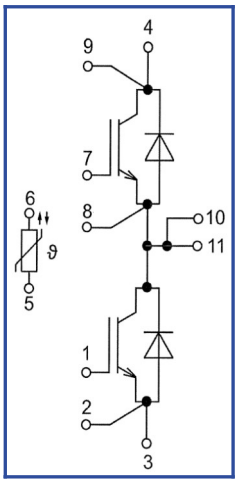
Low Inductance IGBT Module with 17 mm Height Housing — 1700 V 300 A





Chip features

- IGBT chip
  - low $V_{CE(sat)}$ value
  - 10 µs short circuit duration at 150°C
  - square RBSOA of 2xI_C
- FRD chip
  - fast and soft reverse recovery
  - low voltage drop

Design features

- copper baseplate
- Al_2O_3 DBC substrate
- ultrasonic welded power terminals
- improved thermal cycling
- RoHS compliant
- low inductance value

Typical application

- AC motor drives
- solar inverters
- air conditioning
- high power converters and UPS
- Inverters for wind energy converters

Maximum rated values

Definition	Symbol	Conditions	Value	Unit
IGBT				
Collector-Emitter voltage	V_{CES}	V_{GE} = 0.	1700	V
Maximum allowable collector current (continuous)	$I_{C\,25}$	$T_{vj\,(max)}$ = 175°C; T_c = 25°C.	567	A
	$I_{C\,80}$	$T_{vj\,(max)}$ = 175°C; T_c = 80°C.	300	A
Repetitive peak collector current*1	I_{CRM}	I_{CRM} = 2 x $I_{C\,nom}$; t_p = 1 ms.	600	A
Short-circuit duration	t_{psc}	T_{vj} = 25°C; V_{GE} =±15 V; V_{CE} = 1000 V; $R_{G\,on}$ = 3 Ω; $R_{G\,off}$ = 30 Ω	10	µs
		T_{vj} = 150°C; V_{GE} =±15 V; V_{CE} = 1000 V; $R_{G\,on}$ = 3 Ω; $R_{G\,off}$ = 30 Ω	10	
Gate-Emitter voltage	V_{GES}		±20	V
Junction operating temperature	$T_{vj\,(op)}$		-40…+150	°C
Inverse diode \ Freewheeling diode				
Repetitive peak reverse voltage	V_{RRM}	V_{GE} = 0 V.	1700	V
Maximum allowable forward current (continuous)	$I_{F\,25}$	$T_{vj\,(max)}$ = 175°C; T_c = 25°C.	418	A
	$I_{F\,80}$	$T_{vj\,(max)}$ = 175°C; T_c = 80°C.	300	A
Repetitive peak forward current*1	I_{FRM}	I_{FRM} = 2 x $I_{F\,nom}$; t_p = 1 ms.	600	A
Junction operating temperature	$T_{vj\,(op)}$		-40…+150	°C
Module				
Storage temperature	T_{stg}		-55…+50	°C
Isolation voltage	V_{isol}	AC sin 50 Hz; t = 1 min.	4000	V

*1 Pulse width and repetition rate should be such that device junction temperature does not exceed maximum T_{vj} rating

Characteristics

Definition	Symbol	Conditions		Value min.	Value typ.	Value max.	Unit
IGBT							
Collector-Emitter saturation voltage	V_{CEsat}	V_{GE} = +15 V; I_C = 300 A; t_u = 1000 µs.	T_{vj} = 25°C	1.70	1.95	2.25	V
			T_{vj} = 150°C	2.10	2.45	2.90	V
Gate-Emitter threshold voltage	$V_{GE(th)}$	I_C =12 mA; V_{CE} = V_{GE}; T_{vj} = 25°C; t_u = 2 ms.		4.15	6.10	8.10	V
Collector-Emitter cut-off current	I_{CES}	V_{CE} = 1700 V; t_u = 50 ms; V_{GE} = 0.	T_{vj} = 25°C	-	13.00	300	µA
			T_{vj} = 150°C	-	2.00	8.00	mA
Gate-Emitter leakage current	I_{GES}	V_{CE} = 0; V_{GE} = ±20 V; T_{vj} = 25°C; t_u = 30 ms.		-	13.00	200	nA
Input capacitance	C_{ies}	V_{CE} = 25 V; V_{GE} = 0 V; f = 1 MHz; T_{vj} = 25°C.		-	24.00	-	nF
Reverse transfer capacitance	C_{res}			-	0.75	-	nF
Total gate charge	Q_G	I_{Cmax} = 300 A; V_{CE} = 920 V; V_{GE} = - 8÷15 V.		-	-	2500	nC
Internal gate resistance	R_{Gint}	T_{vj} = 25°C.		-	2.83	-	Ω
Turn-on delay time	$t_{d(on)}$	V_{CE} = 920 V; V_{GE} = ±15 V; $I_{C\,max}$ = 300 A; R_G = 3 Ω; L_s = 56 nH.	T_{vj} = 25°C	72	102	127	ns
			T_{vj} = 150°C	87	124	153	ns
Rise time	t_{ri}		T_{vj} = 25°C	32	42	49	ns
			T_{vj} = 150°C	34	45	52	ns
Turn-on energy	E_{on}		T_{vj} = 25°C	25.5	37.0	54.5	mJ
			T_{vj} = 150°C	42.0	62.0	89.5	mJ
Turn-off delay time	$t_{d(off)}$		T_{vj} = 25°C	485	627	710	ns
			T_{vj} = 150°C	592	753	843	ns
Fall time	t_{fi}		T_{vj} = 25°C	309	399	447	ns
			T_{vj} = 150°C	494	638	721	ns
Turn-off energy	E_{off}		T_{vj} = 25°C	53.0	70.0	82.5	mJ
			T_{vj} = 150°C	76.0	101.0	116.0	mJ
Collector-emitter threshold voltage	V_{CE0}	V_{GE} = +15 V; T_{vj} = 150°C; I_{CE1} = 75 A; I_{CE2} = 300 A; t_u = 1000 µs.		-	0.79	0.84	V
On-State slope resistance (IGBT)	r_{CE0}			-	4.73	5.36	mΩ
Thermal resistance junction to case	$R_{th(j-c)}$	DC; I_{CE} = 250±50 A; I_{test} = 1.5 A; V_{GE} = +15 V.		-	-	0.068	K/W
Inverse diode \ Freewheeling diode							
Forward voltage drop	V_F	I_F = 300 A; V_{GE} = 0; t_u = 1000 µs.	T_{vj} = 25°C	1.65	1.90	2.20	V
			T_{vj} = 150°C	1.90	2.20	2.55	V
Reverse recovery time	t_{rr}	V_{GE} = ±15 V; V_{CE} = 920 V; $I_{C\,max}$ = 300 A; $R_{G\,on}$ = 3 Ω; L_s = 56 nH.	T_{vj} = 25°C	200	290	368	ns
			T_{vj} = 150°C	299	439	580	ns
Peak reverse current	I_{RM}		T_{vj} = 25°C	335	460	610	A
			T_{vj} = 150°C	365	490	635	A
Recovered charge	Q_r		T_{vj} = 25°C	49	65	84	µC
			T_{vj} = 150°C	68	97	124	µC
Reverse recovery energy	E_{rec}		T_{vj} = 25°C	38.5	55.0	72.5	mJ
			T_{vj} = 150°C	58.0	85.0	109.0	mJ
Threshold voltage	$V_{(T0)}$	T_{vj} = 150°C; V_{GE} = 0; I_{CE1} = 75 A; I_{CE2} = 300 A; t_u = 1000 µs		-	0.91	0.96	V
Forward slope resistance	r_T			-	3.54	4.19	mΩ
Thermal resistance junction to case	$R_{th(JC-D)}$	DC; I_{CE} = 250±50 A; I_{test} = 1.5 A; V_{GE} = +15 V.		-	-	0.132	K/W

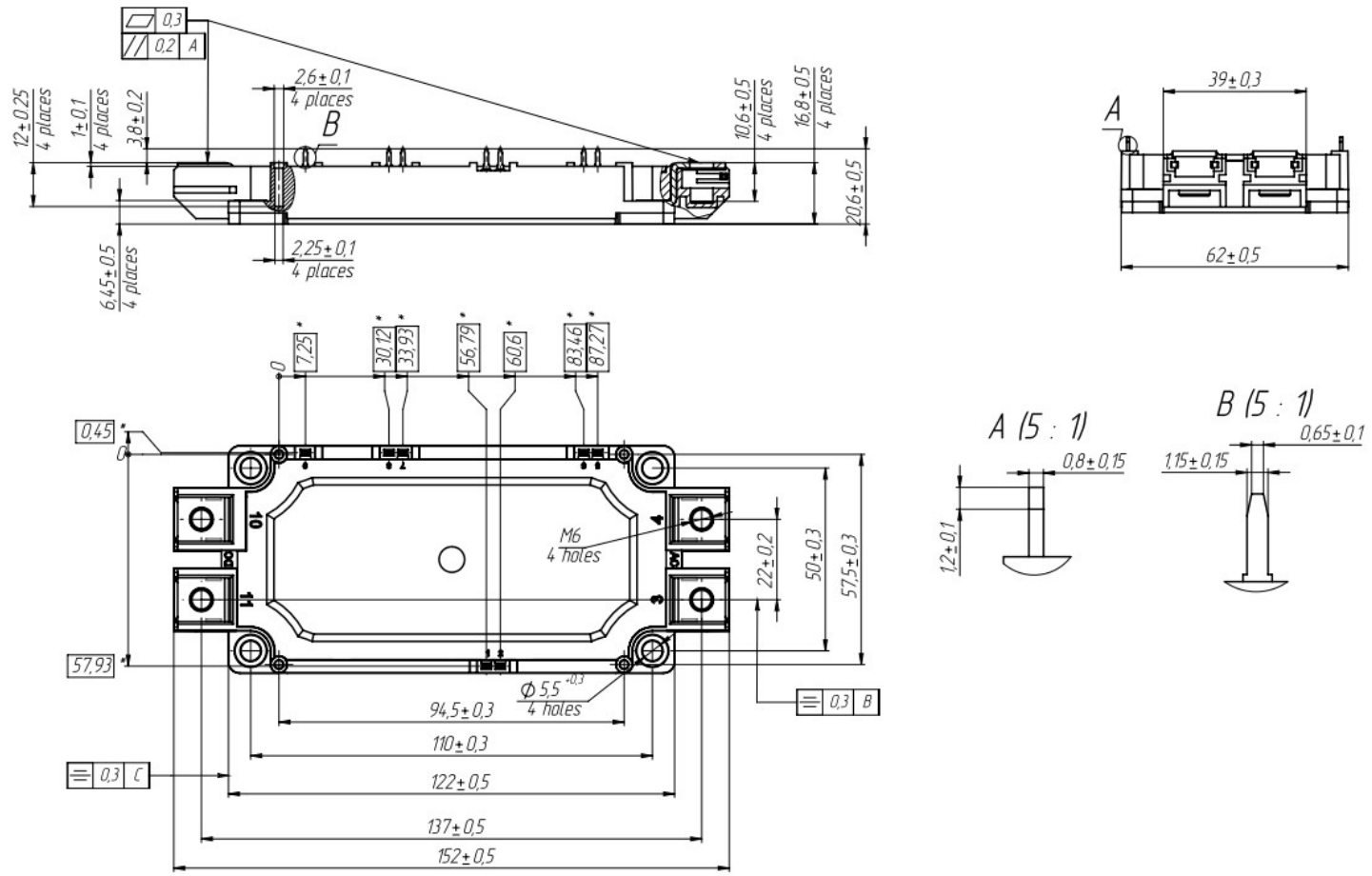
Module							
Pin resistance	R_{Pxy}	T_{vj} = 25°C.	$R_{P10/11-3}$	-	0.92	1.00	mΩ
			$R_{P10/11-4}$	-	0.59	1.00	
Parasitic inductance between terminals	L_{Pce}			-	26	-	nH
Thermistor resistance	R_t	T_{vj} = 25°C		4850	-	6225	Ω
		T_{vj} = 150°C		160	-	195	
Thermal resistance case to heatsink	R_{thCH}	per module		-	0.009	0.014	K/W
Mounting torque for screws to heatsink	M_s	to heatsink M5		3	-	6	N*m
Mounting torque for terminal screws	M_t	to terminals M6		3	-	6	N*m
Weight	W			-	360	-	g

" - " — data will be refined as additional tests are conducted and statistics are collected.

Notes:

- Insulating material operating temperature 125°C max;
- Case temperature 125°C max;
- The recommended operating junction temperature $T_{vj\ op}$ = -40...+150°C.

Overall dimensions: Package type – D2



Part numbering guide

MID2	-	HB	17	LA	-	300	N	
MID2								IGBT module package type: D2
		HB						Half-Bridge
			17					Voltage rating (V_{CES}/100)
				LA				IGBT+FRD chipset modification
						300		Current Rating
							N	Climatic version: normal climate

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